

PBSS4580PA

80 V, 5.6 A NPN low V_{CEsat} (BISS) transistor
Rev. 01 — 15 April 2010

Product data sheet

Product profile

1.1 General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor, encapsulated in an ultra thin SOT1061 leadless small Surface-Mounted Device (SMD) plastic package with medium power capability.

PNP complement: PBSS5580PA.

1.2 Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- Exposed heat sink for excellent thermal and electrical conductivity
- Leadless small SMD plastic package with medium power capability

1.3 Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	80	V
I_{C}	collector current		-	-	5.6	Α
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-	7	Α
R _{CEsat}	collector-emitter saturation resistance	$I_C = 5.6 \text{ A};$ $I_B = 280 \text{ mA}$	<u>[1]</u> -	40	57	mΩ

^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02.$



2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	base		_
2	emitter	3	3
3	collector	1 2 Transparent top view	12 sym021

3. Ordering information

Table 3. Ordering information

Type number	Package	Package		
	Name	Description	Version	
PBSS4580PA	HUSON3	plastic thermal enhanced ultra thin small outline package; no leads; three terminals; body $2 \times 2 \times 0.65$ mm	SOT1061	

4. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4580PA	AD

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

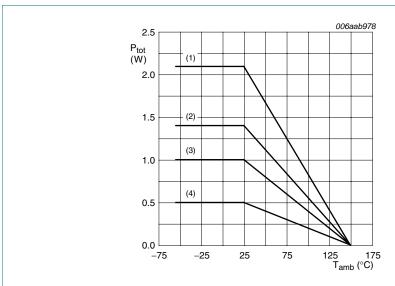
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	80	V
V_{CEO}	collector-emitter voltage	open base	-	80	V
V_{EBO}	emitter-base voltage	open collector	-	6	V
I _C	collector current		-	5.6	Α
I _{CM}	peak collector current	$\begin{array}{l} \text{single pulse;} \\ t_p \leq 1 \text{ ms} \end{array}$	-	7	Α
I _B	base current		-	600	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[1] -	500	mW
			[2] _	1	W
			[3]	1.4	W
			[4] -	2.1	W

Table 5. Limiting values ... continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, mounting pad for collector 1 cm²
- (4) FR4 PCB, standard footprint

Fig 1. Power derating curves

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient		in free air	<u>[1]</u> _	-	250	K/W
		[2]	-	125	K/W	
		[3]	-	90	K/W	
			[4]	-	60	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- 3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

PBSS4580PA_1

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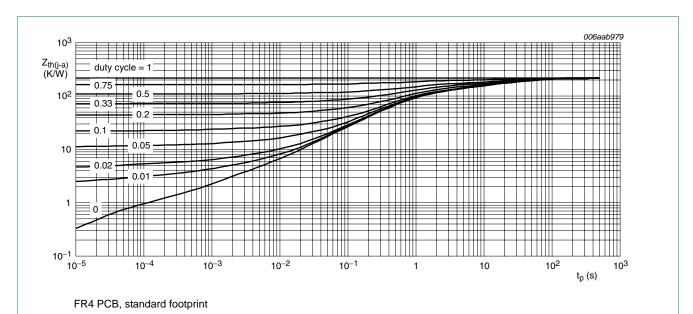
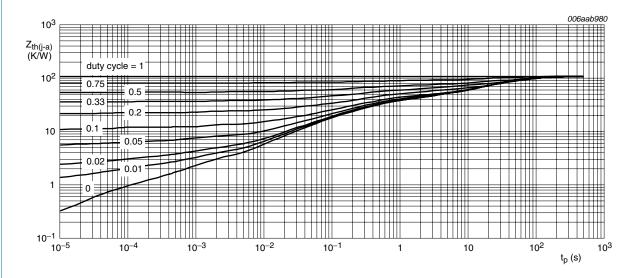


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector 1 cm²

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

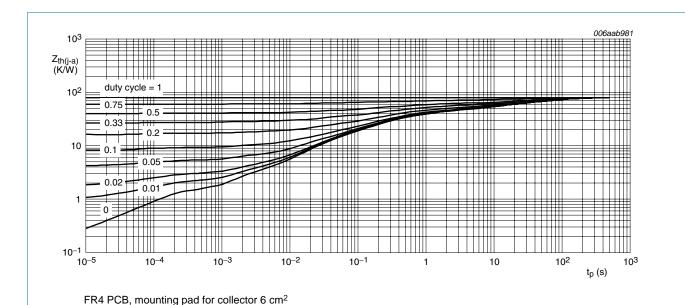
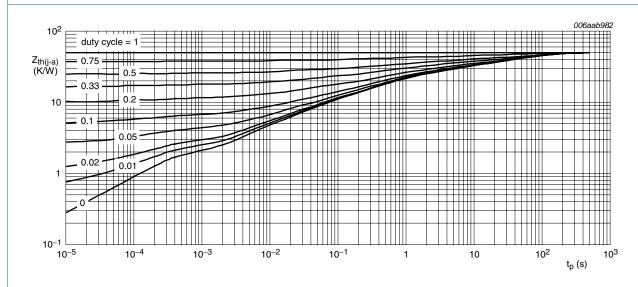


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Ceramic PCB, Al₂O₃, standard footprint

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

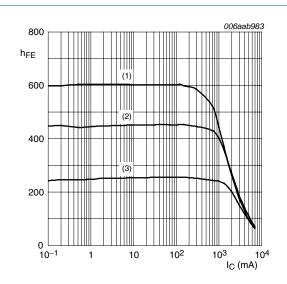
7. Characteristics

Table 7. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base	$V_{CB} = 64 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
	cut-off current	$V_{CB} = 64 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$	-	-	50	μА
I _{CES}	collector-emitter cut-off current	$V_{CE} = 64 \text{ V}; V_{BE} = 0 \text{ V}$	-	-	100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 2 V	[1]			
		$I_C = 0.5 A$	270	425	-	
		I _C = 1 A	240	375	-	
		I _C = 2 A	150	245	-	
	I _C = 6 A	45	75	-		
V _{CEsat}	collector-emitter	$I_C = 0.5 \text{ A}; I_B = 50 \text{ mA}$	<u>[1]</u> -	25	35	mV
	saturation voltage	$I_C = 1 A$; $I_B = 50 \text{ mA}$	[1] -	50	70	mV
		$I_C = 1 A$; $I_B = 10 mA$	<u>[1]</u> -	85	120	mV
		$I_C = 2 A$; $I_B = 20 mA$	<u>[1]</u> -	150	220	mV
		$I_C = 3 A$; $I_B = 30 mA$	<u>[1]</u> -	265	360	mV
		$I_C = 4 A$; $I_B = 400 \text{ mA}$	<u>[1]</u> -	155	210	mV
		$I_C = 5.6 \text{ A}; I_B = 280 \text{ mA}$	<u>[1]</u> -	230	320	mV
R _{CEsat}	collector-emitter saturation resistance	$I_C = 5.6 \text{ A}; I_B = 280 \text{ mA}$	[1] -	40	57	mΩ
V _{BEsat}	base-emitter	$I_C = 1 A; I_B = 10 mA$	<u>[1]</u> -	0.74	0.9	V
	saturation voltage	$I_C = 5.6 \text{ A}; I_B = 280 \text{ mA}$	<u>[1]</u> -	1	1.1	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = 2 \text{ V}; I_{C} = 2 \text{ A}$	[1] -	0.76	0.9	V
t _d	delay time	$V_{CC} = 9 \text{ V}; I_C = 2 \text{ A};$	-	21	-	ns
t _r	rise time	$I_{Bon} = 0.1 \text{ A};$ $I_{Boff} = -0.1 \text{ A}$	-	162	-	ns
t _{on}	turn-on time	- I _{Boff} = −0.1 A	-	183	-	ns
t _s	storage time		-	720	-	ns
t _f	fall time		-	205	-	ns
t _{off}	turn-off time		-	925	-	ns
f⊤	transition frequency	V _{CE} = 10 V; I _C = 100 mA; f = 100 MHz	95	155	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	20	25	pF

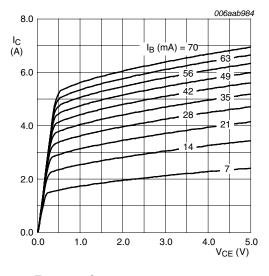
^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$



$$V_{CE} = 2 V$$

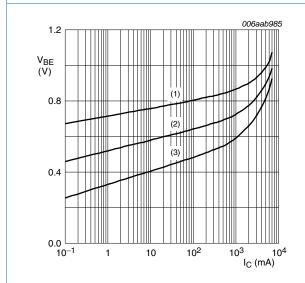
- (1) T_{amb} = 100 °C
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

Fig 6. DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

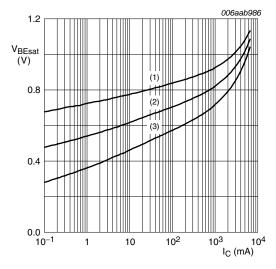
Fig 7. Collector current as a function of collector-emitter voltage; typical values





- (1) $T_{amb} = -55 \,^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 8. Base-emitter voltage as a function of collector current; typical values

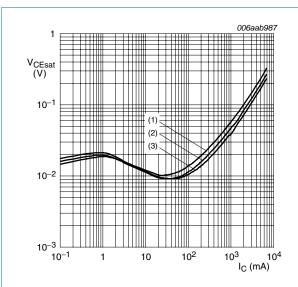


$$I_{\rm C}/I_{\rm B} = 20$$

- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 9. Base-emitter saturation voltage as a function of collector current; typical values

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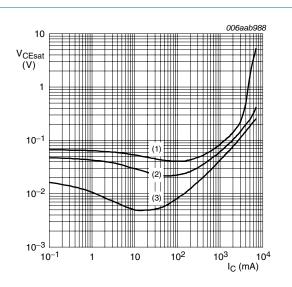
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values

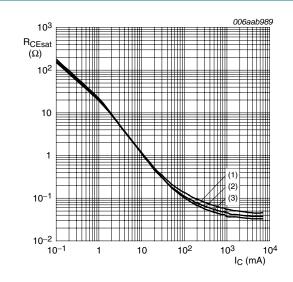


(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig 11. Collector-emitter saturation voltage as a function of collector current; typical values



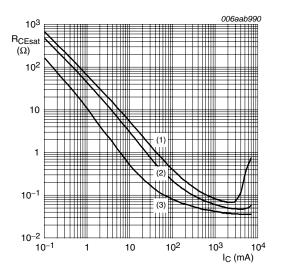
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values



(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig 13. Collector-emitter saturation resistance as a function of collector current; typical values

8. Test information

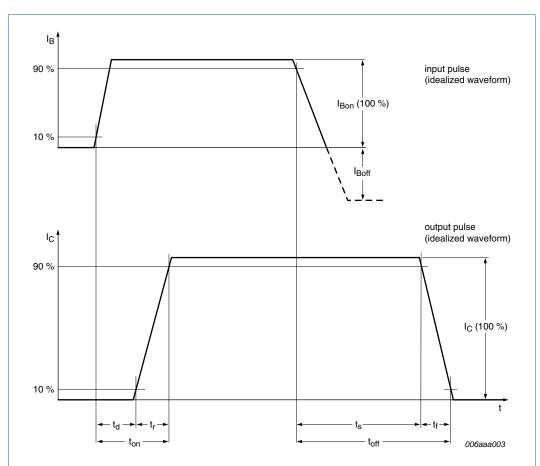


Fig 14. BISS transistor switching time definition

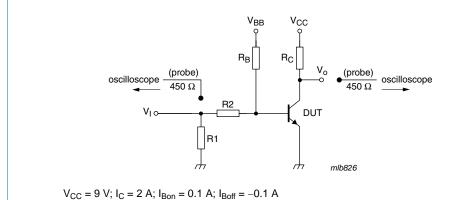
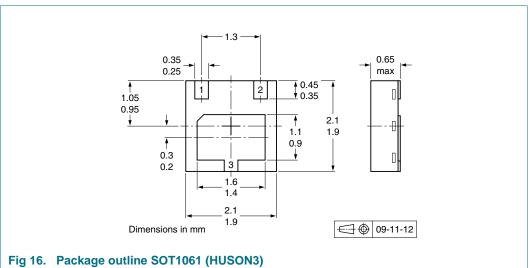


Fig 15. Test circuit for switching times

Package outline



10. Packing information

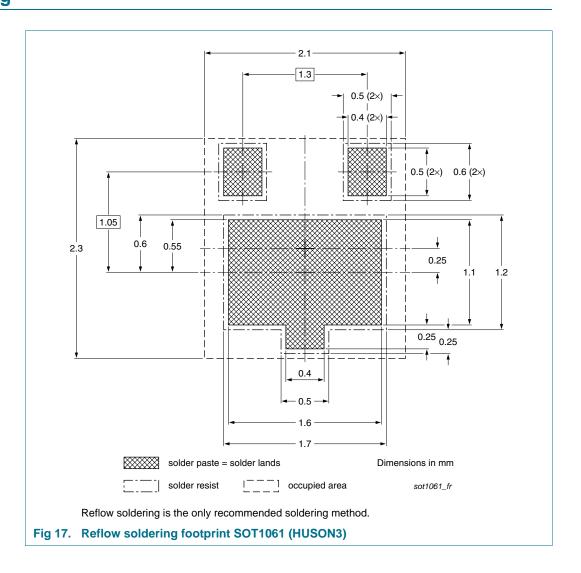
Table 8. **Packing methods**

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity
			3000
PBSS4580PA	SOT1061	4 mm pitch, 8 mm tape and reel	-115

^[1] For further information and the availability of packing methods, see Section 14.

11. Soldering





12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4580PA_1	20100415	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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